



Bipolar NPN Bare Die – BTN6010

Part Description

The BTN6010 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6010.

Key Parameters:

- VCBO = 12V
- VCEO = 12V
- VEBO = 5V
- hFE = 500 @ VCE = 2V, IC = 0.1A
- VCE(Sat) = 0.4V @ IC = 4A, IB = 50mA
- fT = 150 MHz @ VCE = 5V, IE = 0A
- COBO = 40pF @ VCB = 10V

Features

Very Low VCE(sat). Designed to provide performance equivalent to ZETEX / DIODES INC. FZT688 or ROHM 2SD2672

Die Size (Unawn)

1010 μ m X 1010 μ m, 40 Mils X 40 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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